

### General Description

This PAP01T39X P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

BVDSS	RDS(on)	ID
-100V	50mΩ	-30A

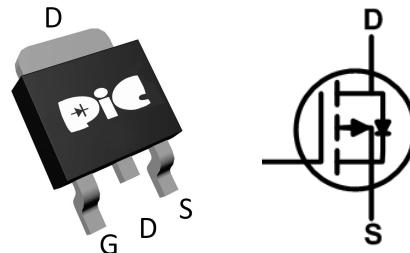
### Feature

- ◆ Super Low Gate Charge
- ◆ 100% EAS Guaranteed
- ◆ Green Device Available
- ◆ Excellent CdV/dt effect decline
- ◆ Advanced high cell density Trench technology

### Application

- ▼ Switching application
- ▼ DC/DC converters
- ▼ Power Tools

### TO252 Pin Configuration



### Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V <sub>DS</sub>	-100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	I <sub>D</sub> @T <sub>c</sub> =25°C	-30	A
Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	I <sub>D</sub> @T <sub>c</sub> =100°C	-19	A
Pulsed Drain Current <sup>2</sup>	I <sub>DM</sub>	-100	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	345	mJ
Avalanche Current	I <sub>AS</sub>	28	A
Total Power Dissipation <sup>4</sup>	P <sub>D</sub> @T <sub>c</sub> =25°C	104	W
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	°C
Operating Junction Temperature Range	T <sub>J</sub>	-55 to 150	°C
Thermal Resistance Junction-Ambient <sup>1</sup>	R <sub>θJA</sub>	62	°C/W
Thermal Resistance Junction-Case <sup>1</sup>	R <sub>θJC</sub>	1.22	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

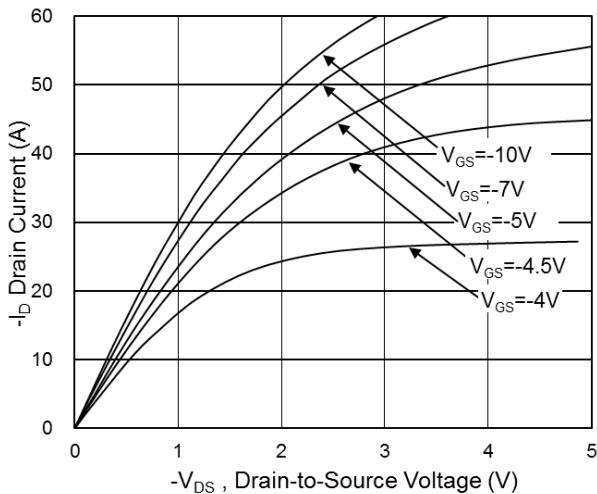
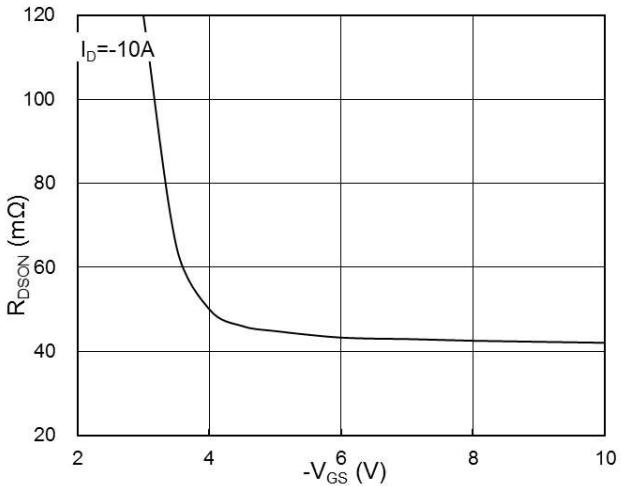
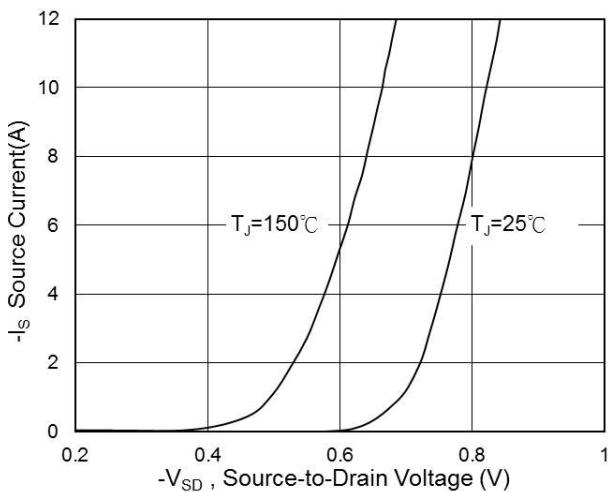
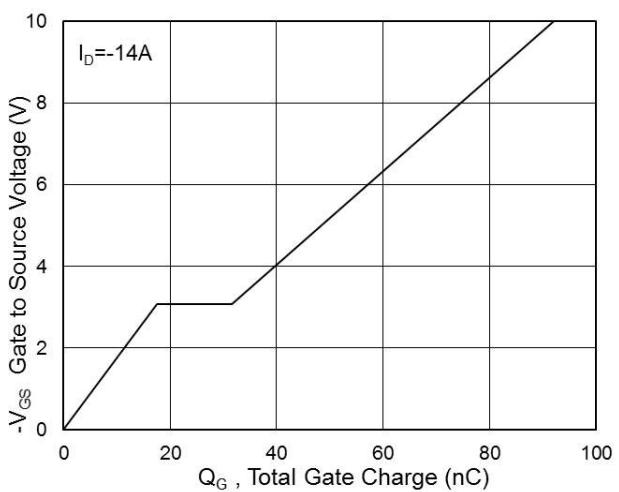
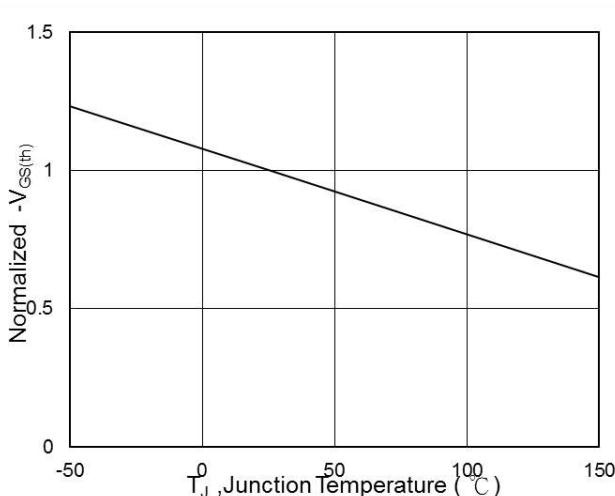
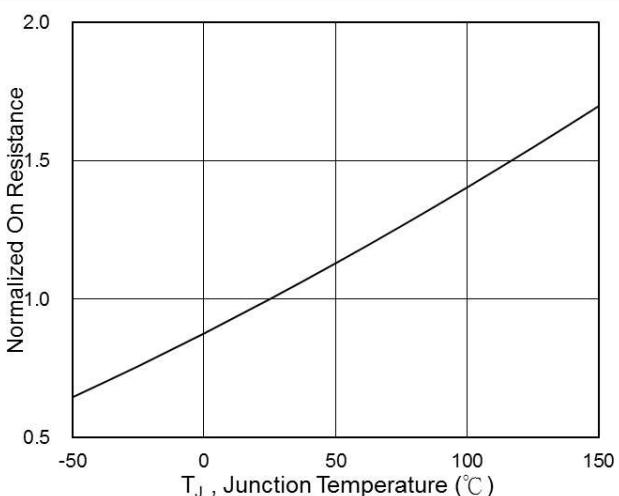
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_{\text{D}}=-250\mu\text{A}$	-100	---	---	V
Static Drain-Source On-Resistance <sup>2</sup>	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}$ , $I_{\text{D}}=-10\text{A}$	---	42	50	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$ , $I_{\text{D}}=-8\text{A}$	---	46	55	
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_{\text{D}}=-250\mu\text{A}$	-1.2	-1.8	-2.5	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-100\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	-50	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=-10\text{V}$ , $I_{\text{D}}=-10\text{A}$	---	32	---	S
Total Gate Charge	$Q_g$	$V_{\text{DS}}=-80\text{V}$ , $V_{\text{GS}}=-10\text{V}$ , $I_{\text{D}}=-14\text{A}$	---	92	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	17.5	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	14	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=-50\text{V}$ , $V_{\text{GS}}=-10\text{V}$ , $R_{\text{G}}=3.3\Omega$ , $I_{\text{D}}=-14\text{A}$	---	20.5	---	ns
Rise Time	$T_r$		---	32.2	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	123	---	
Fall Time	$T_f$		---	63.7	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-25\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	6516	---	pF
Output Capacitance	$C_{\text{oss}}$		---	223	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	125	---	

**Diode Characteristics**

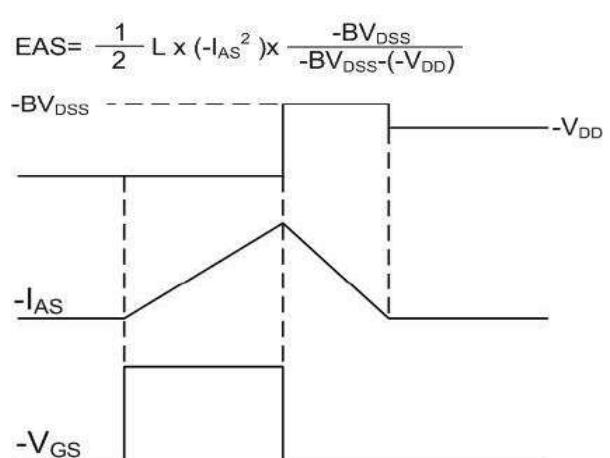
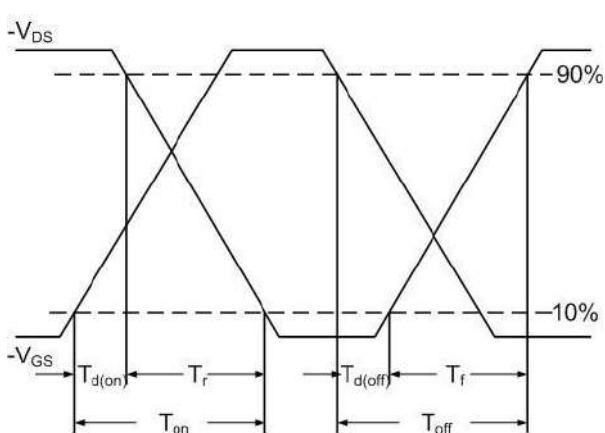
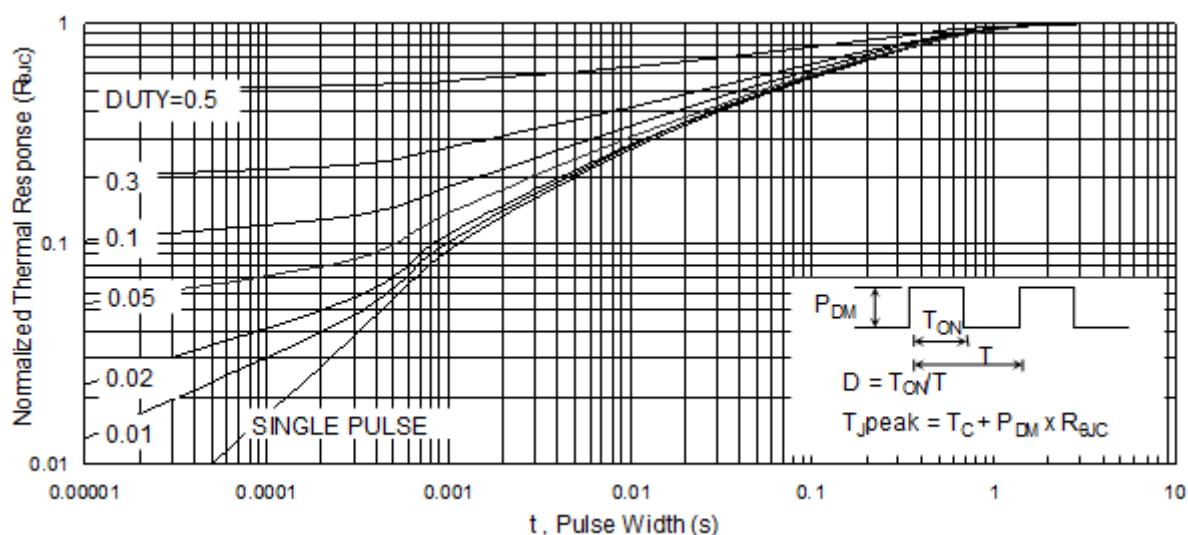
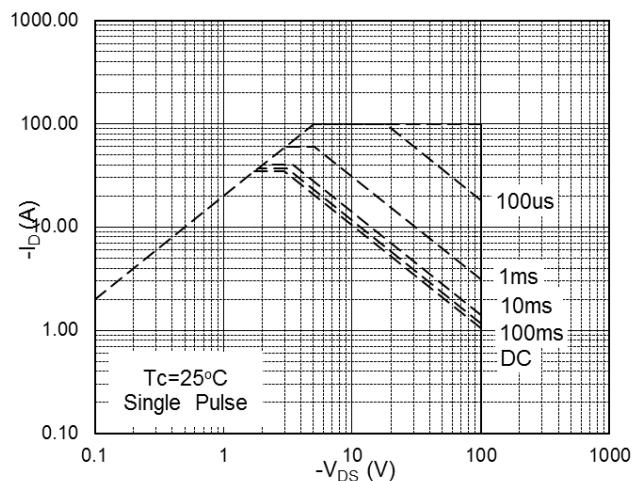
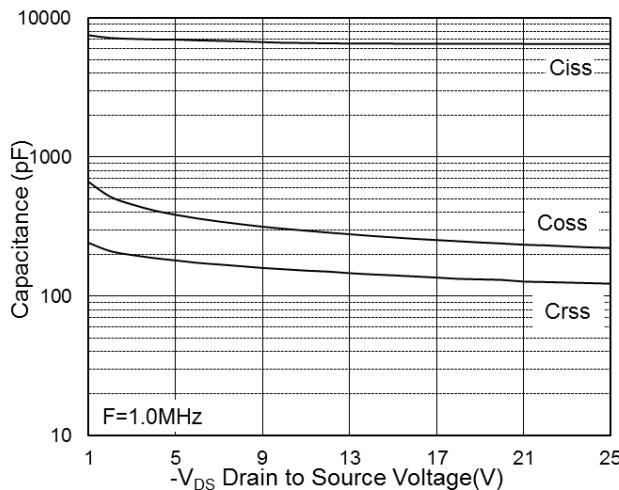
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current <sup>1,5</sup>	$I_s$	$V_G=V_D=0\text{V}$ , Force Current	---	---	-30	A
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_s=-1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.2	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F=-14\text{A}$ , $dI/dt=-100\text{A}/\mu\text{s}$ , $T_J=25^\circ\text{C}$	---	31.2	---	nS
Reverse Recovery Charge	$Q_{\text{rr}}$		---	31.97	---	nC

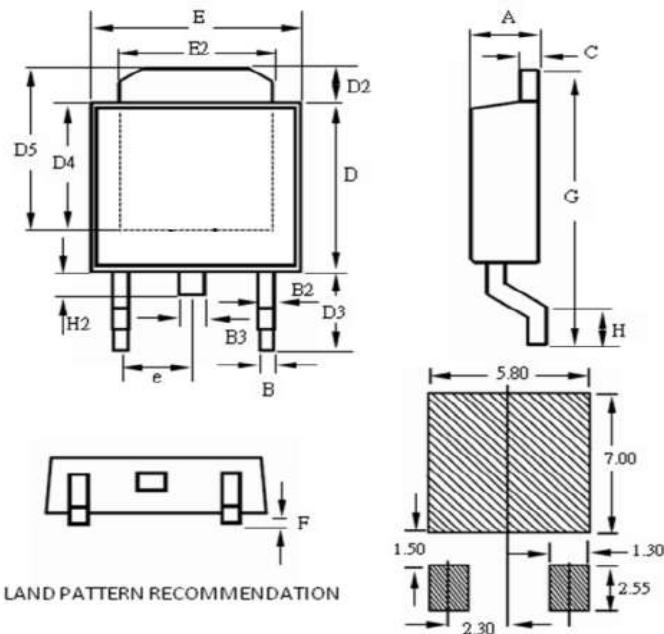
Note :

- 1.Pulse width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=-25\text{V}$ , $V_{\text{GS}}=-10\text{V}$ , $L=0.88\text{mH}$ , $I_{\text{AS}}=-28\text{A}$
- 4.Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .
- 5.The data is theoretically the same as  $I_D$  and  $I_{\text{DM}}$  , in real applications , should be limited by total power dissipation.

**Typical Characteristics**

**Fig.1 Typical Output Characteristics**

**Fig.2 On-Resistance vs G-S Voltage**

**Fig.3 Typical S-D Diode Forward Voltage**

**Fig.4 Gate-Charge Characteristics**

**Fig.5 Normalized  $V_{GS(\text{th})}$  vs  $T_J$** 

**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**

### Typical Characteristics



**TO-252 Package Outline**


SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.10	--	2.50	0.083	--	0.098
B	0.30	--	0.89	0.012	--	0.035
B2	0.40	--	1.14	0.016	--	0.045
B3	0.60	--	1.00	0.024	--	0.039
C	0.40	--	0.89	0.016	--	0.035
D	5.30	--	6.25	0.209	--	0.246
D2	0.50	--	1.70	0.020	--	0.067
D3	2.20	--	3.40	0.087	--	0.134
D4	4.32	--	--	0.170	--	--
D5	5.21	--	--	0.205	--	--
E	6.30	--	6.73	0.248	--	0.265
E2	4.80	--	5.46	0.189	--	0.215
F	0.00	--	0.30	0.000	--	0.012
G	9.20	--	10.41	0.362	--	0.410
H	0.90	--	1.95	0.035	--	0.077
H2	0.50	--	1.10	0.020	--	0.043
e	--	2.30	--	--	0.091	--

**Ordering Information**

Part Number	Description	Quantity
PAP01T39X	TO-252 Reel	2500 pcs

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